

- 2 (146) US-20030109093-A1.DID. (((charge near3 strap\$4 trap\$4 nitride)))
- 2 (147) (((charge near3 strap\$4 trap\$4 nitride)))
- 2 (148) (((charge near3 strap\$4 trap\$4 nitride)))
- 2 (4) "20030109093" 6,670,671.pn
- 2 (4792184) conduct\$4 metal
- 2 (6730) ((insulat\$5 dielectric oxide)) near4 (oxidizing oxidized) with conduct\$4 me
- 2 (145548) first adj2 conduct\$4 metal
- 2 (477) (first adj2 conduct\$4 metal) with ((insulat\$5 dielectric oxide))
- 2 (0) (first adj2 conduct\$4 metal) with ((insulat\$5 dielectric oxide))
- 2 (21) ((first adj2 conduct\$4 metal)) with ((insulat\$5 dielectric oxide))
- 2 (0) ((insulat\$5 dielectric oxide))
- 2 (5749) bird adj beak
- 2 (5749) bird\$2 adj beak
- 2 ((110) (bird adj beak)) and ((sonos monos minos)))
- 2 (38) ((bird adj beak))
- 2 (18) ((insulat\$5 dielectric oxide))
- 2 (2) 6645801.pn
- 2 (2) 6645801.pn. and ((wordline "WL" ((word digit control adj gate) adj line) word ne
- 2 (260209) \$7icid\$4 silicat\$4)
- 2 (2) 6645801.pn. and ((s?icid\$4 silicat\$4))
- 2 (2) 6524913.pn
- 2 (3) diffusion near5 ion adj implantation
- 2 (5553) diffusion near5 ion adj implantation
- 2 (4059053) (source near drain source adj drain drain adj source s/d/s active adj regi
- 2 (820) (diffusion near5 ion adj implantation) with ((source near drain source adj drain
- 2 (4024992) (source near drain source adj drain drain adj source s/d/s)

DBS: USPAT-US-PCPLIB-EPO-IPC-DERVENT-IBM-TDG
 Default operator: OR
 Plurals
 Highlight all the terms initially

((((charge near3 strap\$4 trap\$4 nitride)))
) same ((b1 bitline bit adj line readline read adj line sense adj line) same ((wordline "WL" ((word digit control adj gate) adj line)
 (word near (read\$3 wrt\$3)))
)) and ((sonos monos minos))
)) no1 (((charge near3 strap\$4 trap\$4 nitride)))
) same ((b1 bitline bit adj line readline read adj line sense adj line) same ((wordline "WL" ((word digit control adj gate) adj line)
 (word near (read\$3 wrt\$3)))
)) and ((sonos monos minos))
)) and ((insulat\$5 dielectric oxide))
) near4 (oxidizing oxidized)) ((4173766" | "5168334" | "5284784" | "5349221" | "5717835" | "5768192" | "5988603" |
 "5972751" | "8001689" | "8023085" | "8030871" | "8074915" | "8130453" | "8143608" | "8153487" | "8153471" |
 "8157575" | "8159795" ,PN,6645801,URPN,("5349221" | "5907171" | "6408980",PN,6541818,URPN,("8458861" |
 "6465303" | "2002/0086548",PN,6524913,URPN,("4173766" | "5168334" | "5349221" | "5644533" | "5768192" |
 "5825686" | "5963465" | "5966603" | "6001709" | "6011725" | "6030871" | "6117730" | "6287817" | "6326268",PN,6488865,URPN,) (20030109093" 6,670,671.pn,)

Oct 2004

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U	Invator	Document	Issue	Title	Current	Current	XP	Reviewed	S	C	P	Search	Image	Docs	P
1	<input type="checkbox"/>	Harari, Elyah	US 2003010 20030.3	Multi-state non-volatile integrated circuit me	438/200-257/E21.68	<input type="checkbox"/>	US 200301								
2	<input type="checkbox"/>	Chen, Chien	US 6784483 20040.1	Method for preventing hole and electron mov	257/317-257/315	<input type="checkbox"/>	US 6784483								
3	<input type="checkbox"/>	Sasago, Yosh	US 6870871 20031.3	Nonvolatile semiconductor memory device a	257/319-257/345	<input type="checkbox"/>	US 6870871								
4	<input checked="" type="checkbox"/>	Hansbey, Ma	US 6645801 20031.1	Salicided gate for virtual ground arrays	438/216-257/314	<input type="checkbox"/>	US 6645801								
5	<input type="checkbox"/>	Hansbey, Ma	US 6541816 20030.2	Planar structure for non-volatile memory dev	257/324-257/E21.67	<input type="checkbox"/>	US 6541816								
6	<input type="checkbox"/>	Lin, Hung-Sui	US 6524913 20030.7	Method of fabricating a non-volatile memory	438/201-438/287	<input type="checkbox"/>	US 6524913								
7	<input type="checkbox"/>	Eitan, Boaz	US 5866603 18991.9	NROM fabrication method with a periphery p	438/258-257/E21.67	<input type="checkbox"/>	US 5866603								
8	<input type="checkbox"/>	Eitan, Boaz	US 5768192 19980.1	Non-volatile semiconductor memory cell utili	365/185-257/E29.30	<input type="checkbox"/>	US 5768192								
9	<input type="checkbox"/>	Lee, Thomas	US 2004020 20041.1	Dense arrays and charge storage devices	257/296	<input type="checkbox"/>	US 200402								
10	<input type="checkbox"/>	Vyvoda, Mich	US 2004018 20040.8	Multiple-mode memory and method for formi	365/51	<input type="checkbox"/>	US 200401								

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